Tystar - Tube 5 (Doped Anneal)

Overview

An atmospheric-pressure quartz tube furnace for annealing doped poly-Si and metal-containing wafers. This tool may be used for annealing and glass bonding of wafers containing Al, Cr, and Au, for which there is a maximum allowed temperature of 500 °C.

LMACS Name	Tystar Doped Anneal (tube 5)
Process Area	ANCILLARY
Model	Tytan Mini Series
Vendor	Tystar
Team	Timothy Harrison Aaron Hryciw Glenn Elaschuk

Process Gases

Process Gases	Max Flow (MFC Range)
N2 carrier	1000 sccm
N2 BKFL	5000 sccm
H2	1000 sccm

Temperature Ranges

Zone	Min	Max
1	500 C	1100 C
2	500 C	1100 C
3	500 C	1100 C

Standard Process Parameters

Table to highlight system features these can be displayed in the format that makes the most sense for the tool. The table below is an example using an ICP-RIE

Temperature				
Duration				

Documents

Operating Procedure	Tystar SOP
Hazard Assessment	

Related Documents

- Tystar - Tube 5 (Doped Anneal) (Equipment)
  - tystar
  - tube5
  - equipment
  - ancillary